

#4

Access DB# 248149

SEARCH REQUEST FORM

Scientific and Technical Information Center

Requester's Full Name: Sin J. Lee Examiner #: 76060 Date: 1-9-08
Art Unit: 1795 Phone Number 30 2-1333 Serial Number: 10/563,501
Mail Box and Bldg/Room Location: 9C15 Results Format Preferred (circle): PAPER DISK E-MAIL
(Rem)

If more than one search is submitted, please prioritize searches in order of need.

Please provide a detailed statement of the search topic, and describe as specifically as possible the subject matter to be searched. Include the elected species or structures, keywords, synonyms, acronyms, and registry numbers, and combine with the concept or utility of the invention. Define any terms that may have a special meaning. Give examples or relevant citations, authors, etc, if known. Please attach a copy of the cover sheet, pertinent claims, and abstract.

Title of Invention: Plz. See B:6.

Inventors (please provide full names):

Earliest Priority Filing Date:

For Sequence Searches Only Please include all pertinent information (parent, child, divisional, or issued patent numbers) along with the appropriate serial number.

Please search for the polymers of
Cl. #1

SCIENTIFIC REFERENCE BR
Sci & Tech Inf. Ctr.
JAN 11 1998
Pat. & T.M. Office

STAFF USE ONLY

Searcher: EJ
Searcher Phone #: _____
Searcher Location: _____
Date Searcher Picked Up: _____
Date Completed: 1-15-08
Searcher Prep & Review Time: _____
Clerical Prep Time: _____
Online Time: _____

Type of Search

NA Sequence (#) _____
AA Sequence (#) _____
Structure (#) _____
Bibliographic _____
Litigation _____
Fulltext _____
Patent Family _____
Other _____

Vendors and cost where applicable

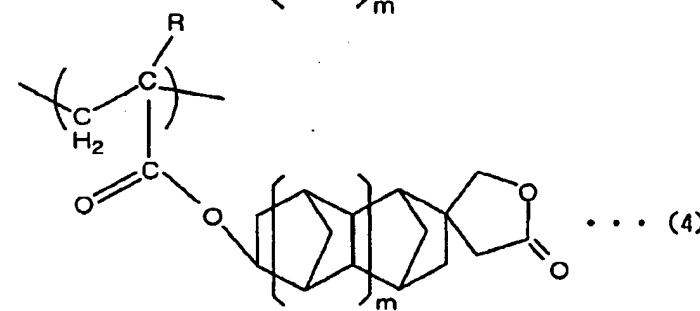
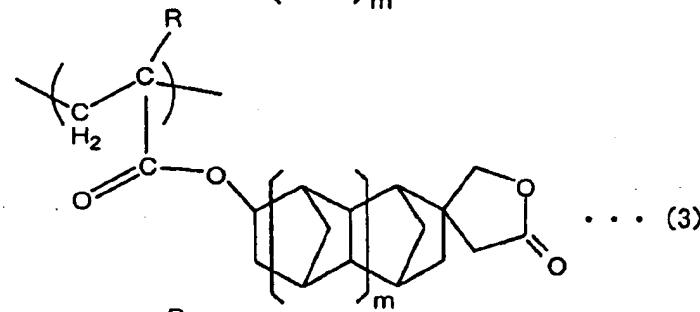
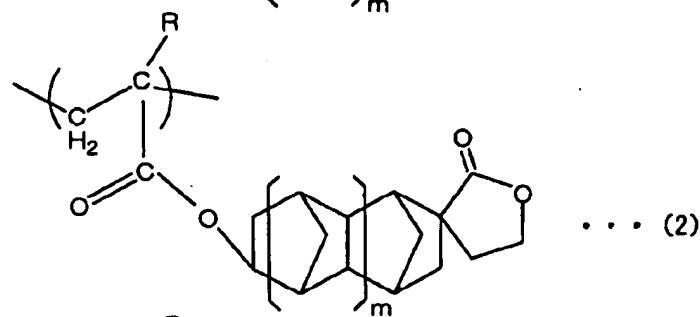
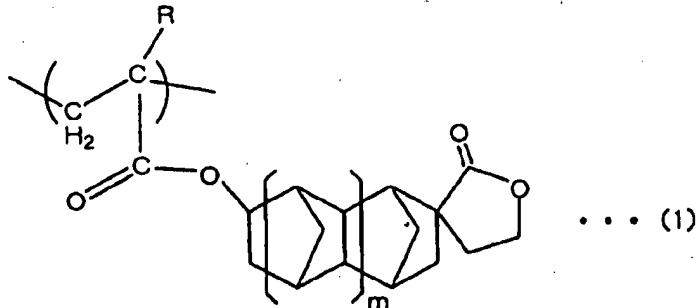
STN _____
Dialog _____
Questel/Orbit _____
Dr. Link _____
Lexis/Nexis _____
Sequence Systems _____
WWW/Internet _____
Other (specify) _____

PTO-1590 (8-01)

Appl. No. : Unknown
Filed : Herewith

AMENDMENTS TO THE CLAIMS

1. (Original) A polymer comprising at least one structural unit (a1) containing a lactone represented by one of general formulas (1) through (4) shown below:



(wherein, in said formulas (1) to (4), R represents a hydrogen atom or a methyl group, and m is either 0 or 1).

=> FILE REG

FILE 'REGISTRY' ENTERED ON 15 JAN 2008
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=> D HIS

FILE 'LREGISTRY' ENTERED ON 15 JAN 2008
 L1 STR

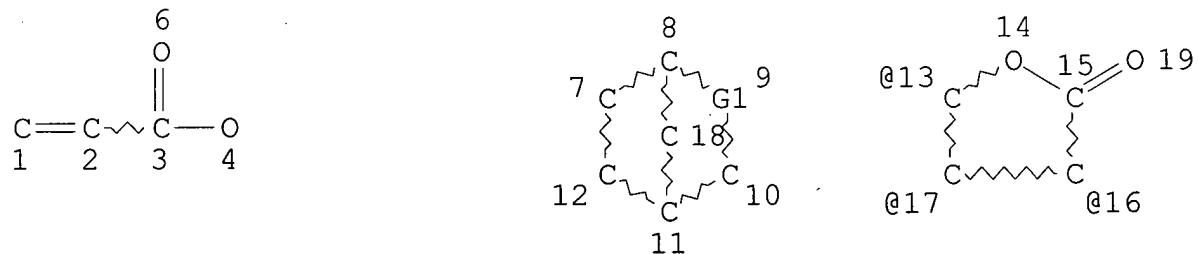
FILE 'REGISTRY' ENTERED ON 15 JAN 2008
 L2 SCR 2043
 L3 1 S L1 AND L2
 L4 25 S L1 AND L2 FUL
 SAV L4 LEE501/A

FILE 'ZCA' ENTERED ON 15 JAN 2008
 L5 15 S L4
 L6 6 S 1840-2003/PY, PRY, AY AND L5

FILE 'REGISTRY' ENTERED ON 15 JAN 2008

=> D L4 QUE STAT

L1 STR



VAR G1=13/16

NODE ATTRIBUTES:

DEFAULT MLEVEL IS ATOM

DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:

RING(S) ARE ISOLATED OR EMBEDDED

NUMBER OF NODES IS 18

STEREO ATTRIBUTES: NONE

L2 SCR 2043

L4 25 SEA FILE=REGISTRY SSS FUL L1 AND L2

100.0% PROCESSED 2969 ITERATIONS
SEARCH TIME: 00.00.01

25 ANSWERS

=> FILE ZCA
FILE 'ZCA' ENTERED ON 15 JAN 2008
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=> D L6 1-6 CBIB ABS HITSTR HITRN

L6 ANSWER 1 OF 6 ZCA COPYRIGHT 2008 ACS on STN
142:363804 Lactone-containing polymers, resist materials containing them with low line edge roughness and excellent resolution, etching resistance, and thermal stability, and pattern formation using them. Funatsu, Akiyuki; Nishi, Tsunehiro; Nagura, Shigehiro (Shin-Etsu Chemical Industry Co., Ltd., Japan). Jpn. Kokai Tokkyo Koho JP 2005097533 A 20050414, 58 pp. (Japanese). CODEN: JKXXAF.
APPLICATION: JP 2004-144569 20040514. PRIORITY: JP 2003-311056 20030903.

AB The polymers, useful for excimer laser photolithog. or electron beam lithog., have repeating units CH₂CR₁(CO₂Z), CH₂CR₃(CO₂Y), and CH₂CR₄(CO₂X) (R_{1,3,4} = H, Me; X = lactone-contg. group; Y = 3-OH-5-R₅-6-R₆-adamantyl; Z = 1-R₂-cyclopentyl, 1-R₂-cyclohexyl; R₂ = C₁₋₁₂ linear, branched, or cyclic alkyl; R_{5,6} = H, OH).

IT **849060-37-3 849060-39-5**

(lactone-contg. polymers for resists with low line edge roughness and good resoln., etching resistance, and thermal stability)

RN 849060-37-3 ZCA

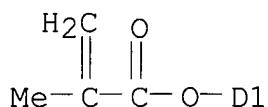
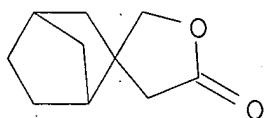
CN 2-Propenoic acid, 2-methyl-, dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3' (2'H)-furan]-5(or 6)-yl ester, polymer with dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3' (2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, 1-ethylcyclopentyl 2-methyl-2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6

CMF C14 H18 O4

CCI IDS

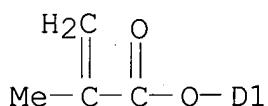
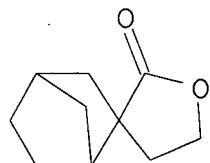


CM 2

CRN 848143-97-5

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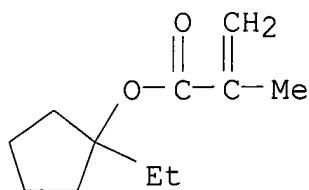
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CM 3

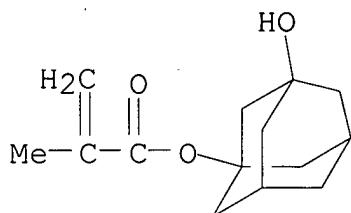
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CMF C11 H18 O2



CM 4

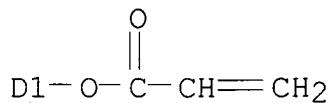
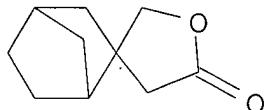
CRN 115372-36-6
 CMF C14 H20 O3



RN 849060-39-5 ZCA
 CN 2-Propenoic acid, 2-methyl-, 1-ethylcyclopentyl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate (9CI) (CA INDEX NAME)

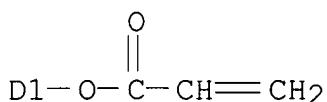
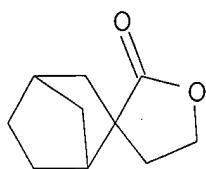
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 CCI IDS



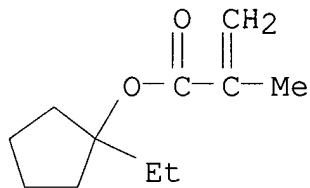
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 CCI IDS



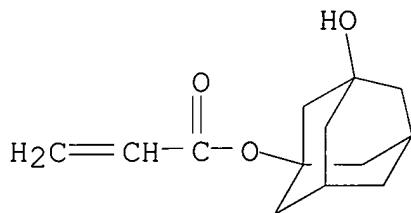
CM 3

CRN 266308-58-1
 CMF C11 H18 O2



CM 4

CRN 216581-76-9
 CMF C13 H18 O3



IT 849060-37-3 849060-39-5

(lactone-contg. polymers for resists with low line edge roughness and good resoln., etching resistance, and thermal stability)

L6 ANSWER 2 OF 6 ZCA COPYRIGHT 2008 ACS on STN
 142:325926 Polymer, resist composition and patterning process.

Tachibana, Seiichiro; Nishi, Tsunehiro; Kobayashi, Tomohiro (Japan).
 U.S. Pat. Appl. Publ. US 2005058938 A1 20050317, 46 pp.
 (English). CODEN: USXXCO: APPLICATION: US 2004-936753 20040909.
 PRIORITY: JP 2003-320659 20030912.

GI

* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY - AVAILABLE VIA OFFLINE PRINT *

AB A polymer comprises recurring units of formulas I, II, III, IV (R1-3,4,7 = H, Me; R2 = acid labile group; R5,6 = H, hydroxyl; R8 = lactone structure group) and has a Mw of 1,000-50,000. A resist compn. comprising the inventive polymer has a sensitivity to high-energy radiation, improved resoln. and etching resistance and lends itself to lithog. micropatterning with electron beams or deep UV.

IT **848143-99-7P 848144-00-3P 848144-01-4P**
848144-02-5P 848144-03-6P

(polymer, resist compn. for patterning process)

RN 848143-99-7 ZCA

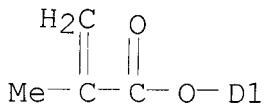
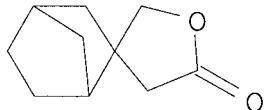
CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate and 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6

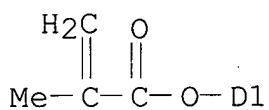
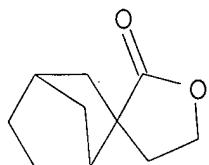
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CCI IDS



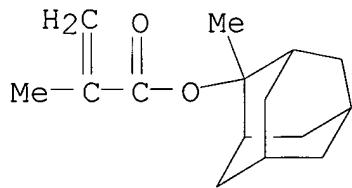
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CRN 848143-97-5
 CMF C14 H18 O4
 CCI IDS



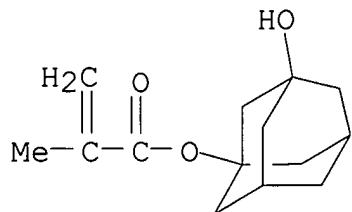
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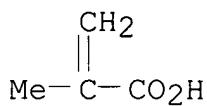


CM 4

CRN 115372-36-6
 CMF C14 H20 O3

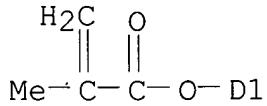
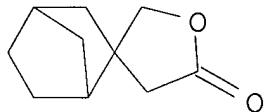


CM 5

CRN 79-41-4
CMF C4 H6 O2

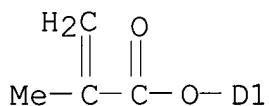
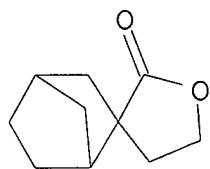
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CM 1

CRN 848143-98-6
CMF C14 H18 O4
CCI IDS

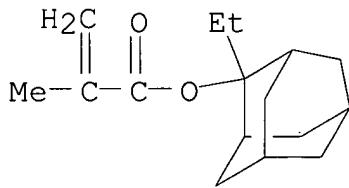
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CRN 848143-97-5
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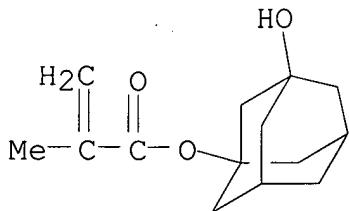
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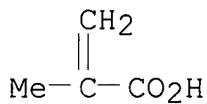
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CRN 115372-36-6
 CMF C14 H20 O3



CM 5

CRN 79-41-4
 CMF C4 H6 O2



RN 848144-01-4 ZCA

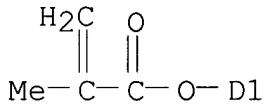
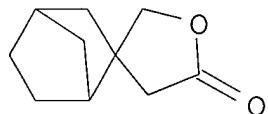
CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, 2-ethylbicyclo[2.2.1]hept-2-yl 2-methyl-2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6

CMF C14 H18 O4

CCI IDS

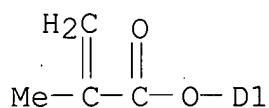
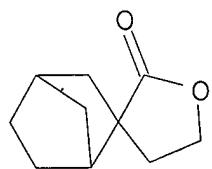


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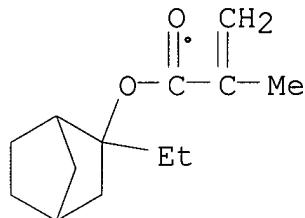
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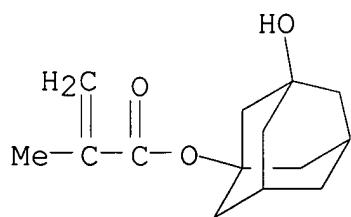
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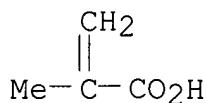
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CM 5

CRN 79-41-4
 CMF C4 H6 O2



RN 848144-02-5 ZCA

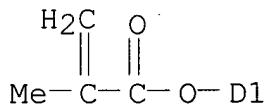
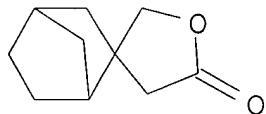
CN 2-Propenoic acid, 2-methyl-, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-methyl-2-propenoate, 2-ethyldecahydro-1,4:5,8-dimethanonaphthalen-2-yl 2-methyl-2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 848143-98-6

CMF C14 H18 O4

CCI IDS

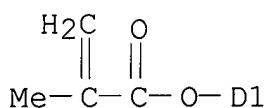
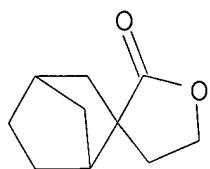


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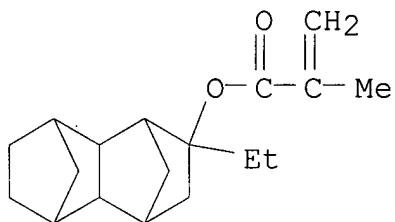
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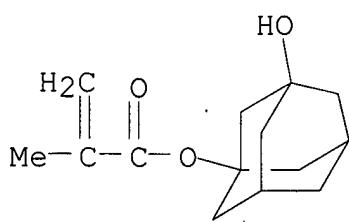
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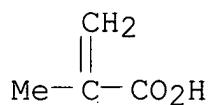
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CM 5

CRN 79-41-4
 CMF C4 H6 O2



RN 848144-03-6 ZCA

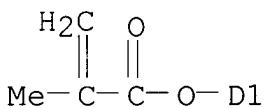
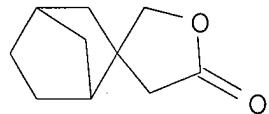
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CM 1

CRN 848143-98-6

CMF C14 H18 O4

CCI IDS

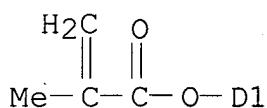
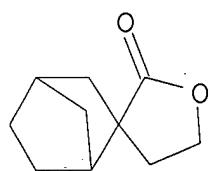


CM 2

CRN 848143-97-5

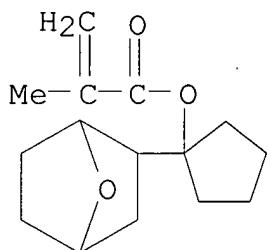
CMF C14 H18 O4

CCI IDS



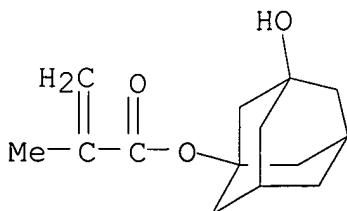
CM 3

CRN 676456-72-7
 CMF C15 H22 O3



CM 4

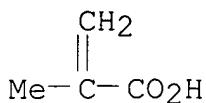
CRN 115372-36-6
 CMF C14 H20 O3



CM 5

CRN 79-41-4

CMF C4 H6 O2



IT **848143-99-7P 848144-00-3P 848144-01-4P**
848144-02-5P 848144-03-6P
 (polymer, resist compn. for patterning process)

L6 ANSWER 3 OF 6 ZCA COPYRIGHT 2008 ACS on STN
 142:123189 Positive resist composition and method for forming resist pattern using same. Hada, Hideo; Miyairi, Miwa; Iwai, Takeshi (Tokyo Ohka Kogyo Co., Ltd., Japan). PCT Int. Appl. WO 2005003193 A1 20050113, 44 pp. DESIGNATED STATES: W: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW; RW: AT, BE, BF, BJ, CF, CG, CH, CI, CM, CY, DE, DK, ES, FI, FR, GA, GB, GR, IE, IT, LU, MC, ML, MR, NE, NL, PT, SE, SN, TD, TG, TR. (Japanese). CODEN: PIXXD2. APPLICATION: WO 2004-JP9620 20040630. PRIORITY: JP 2003-192895 20030707; JP 2004-100204 20040330.

GI

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PMS. Inv.

* STRUCTURE DIAGRAM TOO LARGE FOR DISPLAY - AVAILABLE VIA OFFLINE PRINT *

AB A resist compn. is disclosed which enables to prevent surface roughening of a resist pattern after either etching or developing, or preferably after both etching and developing. A resist pattern is formed by using a pos. resist compn. comprising a resin component (A), an acid-forming agent component (B) which produces an acid when exposed, and an org. solvent (C). The resin component (A) contains at least one constitutional unit (a1) contg. lactone which is represented by one of general formulas I-IV: (R = H, Me; m = 0, 1), and the alkali solv. thereof is increased by the action of an acid.

IT **823810-78-2P 823810-79-3P 823810-80-6P**
823817-70-5P

(resin in pos. resist compn.)

RN 823810-78-2 ZCA

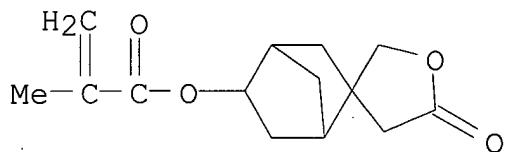
CN 2-Propenoic acid, 2-methyl-, dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer

with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate and 2-methyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-43-0

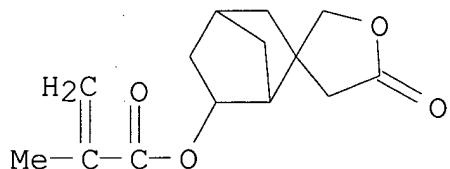
CMF C14 H18 O4



CM 2

CRN 479072-42-9

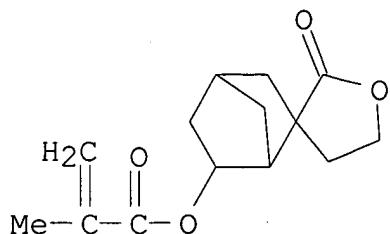
CMF C14 H18 O4



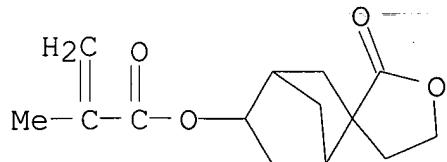
CM 3

CRN 479072-41-8

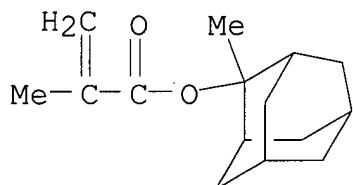
CMF C14 H18 O4



CM 4

CRN 479072-40-7
CMF C14 H18 O4

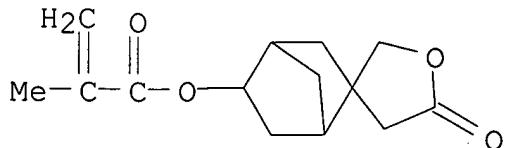
CM 5

CRN 177080-67-0
CMF C15 H22 O2

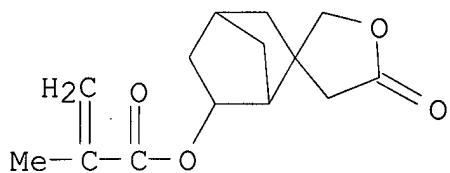
RN 823810-79-3 ZCA

CN 2-Propenoic acid, 2-methyl-, dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate and 2-ethyltricyclo[3.3.1.13,7]dec-2-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

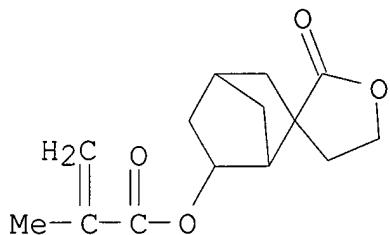
CM 1

CRN 479072-43-0
CMF C14 H18 O4

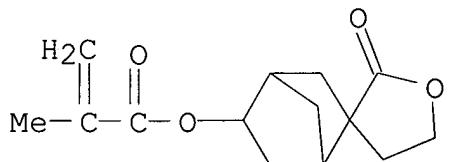
CM 2

CRN 479072-42-9
CMF C14 H18 O4

CM 3

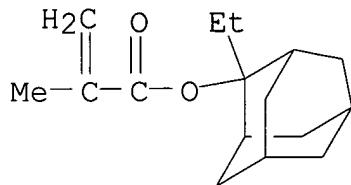
CRN 479072-41-8
CMF C14 H18 O4

CM 4

CRN 479072-40-7
CMF C14 H18 O4

CM 5

CRN 209982-56-9
CMF C16 H24 O2



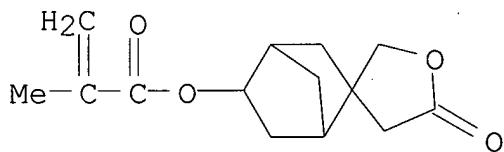
RN 823810-80-6 ZCA

CN 2-Propenoic acid, 2-methyl-, dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-methyl-2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-methyl-2-propenoate and 2-ethyltricyclo[3.3.1.13,7]dec-2-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-43-0

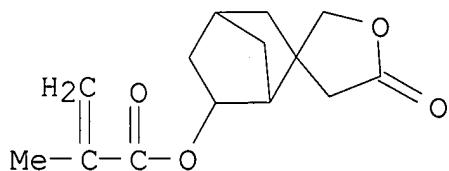
CMF C14 H18 O4



CM 2

CRN 479072-42-9

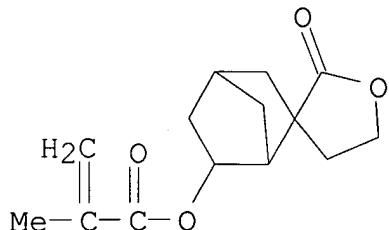
CMF C14 H18 O4



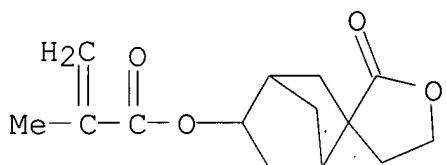
CM 3

CRN 479072-41-8

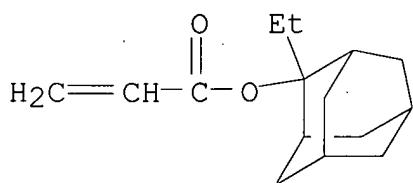
CMF C14 H18 O4



CM 4

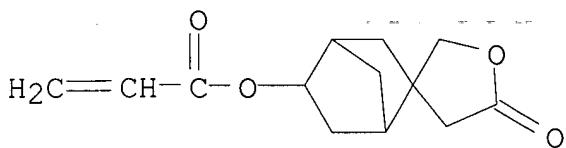
CRN 479072-40-7
CMF C14 H18 O4

CM 5

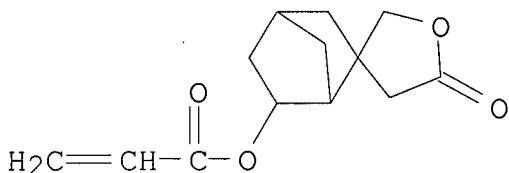
CRN 303186-14-3
CMF C15 H22 O2

RN 823817-70-5 ZCA
 CN 1,4:5,8-Dimethanonaphthalene-2-carboxylic acid, decahydro-6(or 7)-[(1-oxo-2-propenyl)oxy]-, 1,1-dimethylethyl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-propenoate, dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-propenoate, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl 2-propenoate and dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-6-yl 2-propenoate (9CI) (CA INDEX NAME)

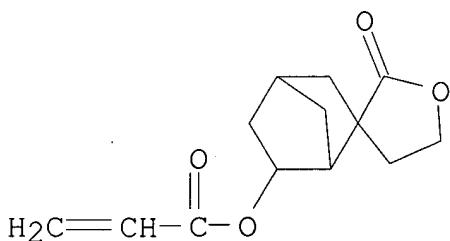
CM 1

CRN 479072-47-4
CMF C13 H16 O4

CM 2

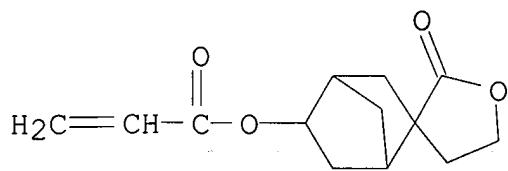
CRN 479072-46-3
CMF C13 H16 O4

CM 3

CRN 479072-45-2
CMF C13 H16 O4

CM 4

CRN 479072-44-1
CMF C13 H16 O4

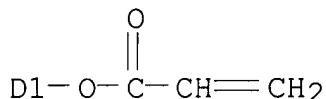
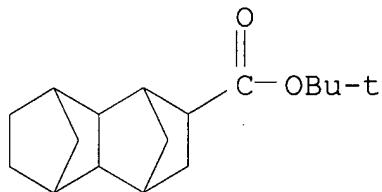


CM 5

CRN 217652-52-3

CMF C20 H28 O4

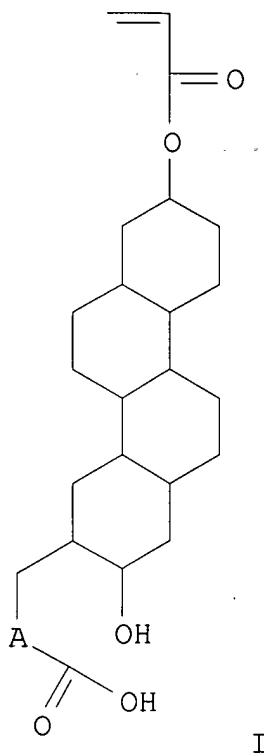
CCI IDS

IT 823810-78-2P 823810-79-3P 823810-80-6P
823817-70-5P

(resin in pos. resist compn.)

L6 ANSWER 4 OF 6 ZCA COPYRIGHT 2008 ACS on STN
 141:417915 Preparation of hydroxy oxide compound, negative-working
 resist using it, and, manufacture of wiring. Yokoyama, Yoshiyuki;
 Hattori, Takashi; Iwashita, Atsushi; Tachikawa, Toshikazu (Tokyo
 Ohka Kogyo Co., Ltd., Japan; Hitachi Ltd.). Jpn. Kokai Tokkyo Koho
 JP 2004317575 A 2004-11-11, 17 pp. (Japanese). CODEN: JKXXAF.
 APPLICATION: JP 2003-107908 20030411.

GI



AB The hydroxy oxide compd. is obtained by the steps of (i) removing metal impurity in a compd. (A) bearing lactone group in the side chain and (ii) opening the lactone ring of the compd. A by hydrolysis using an org. alk. compd. Neg.-working resist compn. contains the hydroxy oxide compd. The hydroxy oxide compd. may I (A = N, S, Cl-21 alkyl), for example. The wiring is manufd. by the steps of (1) forming a layer of the neg. resist contg. resin contg. the hydroxy oxide and an acid generator, (2) exposing and developing the resist for pattern formation, (3) etching the substrate by using the pattern as a mask, and (4) removing the residual resist pattern. As metal impurity content is lowered and clear resist pattern is obtained.

IT **790665-51-9DP**, hydrolyzed

(neg. resist contg. purified hydroxy oxide compd. prep'd. by hydrolysis of lactone ring by org. alk. compd.)

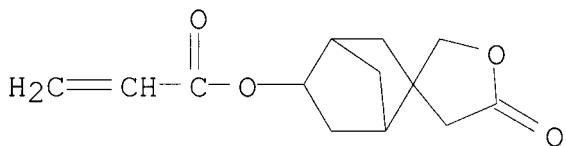
RN 790665-51-9 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'-(2'H)-furan]-5-yl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4

CMF C13 H16 O4

IT **790665-51-9P**

(purifn. and hydrolysis of; neg. resist contg. purified hydroxy oxide compd. prep'd. by hydrolysis of lactone ring by org. alk. compd.)

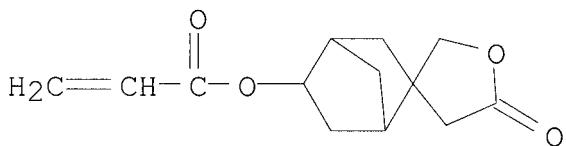
RN 790665-51-9 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, homopolymer (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4

CMF C13 H16 O4

IT **790665-51-9DP**, hydrolyzed

(neg. resist contg. purified hydroxy oxide compd. prep'd. by hydrolysis of lactone ring by org. alk. compd.)

IT **790665-51-9P**

(purifn. and hydrolysis of; neg. resist contg. purified hydroxy oxide compd. prep'd. by hydrolysis of lactone ring by org. alk. compd.)

L6 ANSWER 5 OF 6 ZCA COPYRIGHT 2008 ACS on STN

141:358084 Negative-working resist material and patterning method.

Iwashita, Atsushi; Tachikawa, Toshikazu (Tokyo Ohka Kogyo Co., Ltd., Japan). Jpn. Kokai Tokkyo Koho JP 2004294638 A 20041021, 19 pp. (Japanese). CODEN: JKXXAF. APPLICATION: JP 2003-84981 20030326.

AB Disclosed is the neg.-working resist material comprising a polymer compd. and a photoacid, wherein the polymer compd. has a polymerizable unit bonded to the backbone chain via C of a hydroxy acid and has no space between the hydroxy acid and the backbone chain not to admit an alkali substance close to it. The hydroxy acid group bonded to the backbone chain improved the storage stability and the space resoln.

IT **776329-02-3P 776329-03-4P**

(neg.-working resist material having hydroxy acid group bonded to backbone chain)

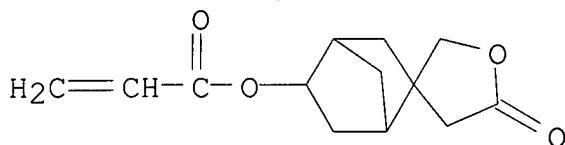
RN 776329-02-3 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5-yl ester, polymer with dihydro-4,4-dimethyl-3-methylene-2(3H)-furanone and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 479072-47-4

CMF C13 H16 O4

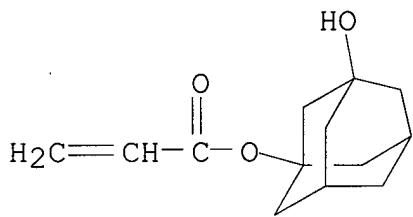


present (3)

CM 2

CRN 216581-76-9

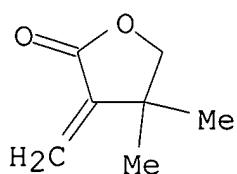
CMF C13 H18 O3



CM 3

CRN 135102-85-1

CMF C7 H10 O2



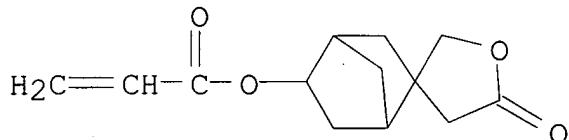
RN 776329-03-4 ZCA

CN 2-Propenoic acid, dihydro-5'-oxospiro[bicyclo[2.2.1]heptane-

2,3' (2'H)-furan]-5-yl ester, polymer with hexahydro-2-oxo-3,5-methano-2H-cyclopenta[b]furan-6-yl 2-propenoate and 3-hydroxytricyclo[3.3.1.13,7]dec-1-yl 2-propenoate (9CI) (CA INDEX NAME)

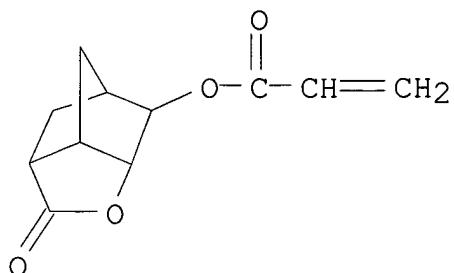
CM 1

CRN 479072-47-4
CMF C13 H16 O4



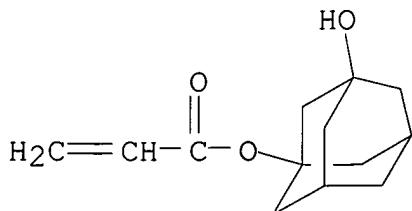
CM 2

CRN 242129-35-7
CMF C11 H12 O4



CM 3

CRN 216581-76-9
CMF C13 H18 O3



IT 776329-02-3P 776329-03-4P

(neg.-working resist material having hydroxy acid group bonded to

backbone chain)

L6 ANSWER 6 OF 6 ZCA COPYRIGHT 2008 ACS on STN

139:188311 Positive DUV resist compositions with suppressed roughness of etched surfaces and good dissolution and defocus latitude in contact hole pattern formation. Sato, Kenichiro (Fuji Photo Film Co., Ltd., Japan). Jpn. Kokai Tokkyo Koho JP 2003233187 A **20030822**, 54 pp. (Japanese). CODEN: JKXXAF. APPLICATION: JP 2002-32448 20020208.

GI



AB The pos. resist compns. contain (A) 2 resins contg. specific repeating units bearing alicyclic groups and (B) compds. which generate acids by irradn. of actinic ray or radiation. A comprise (A1) resins bearing repeating units represented by $\text{CH}_2\text{CR}_1\text{ACO}_2\text{ALG}$ [$\text{R}_1 = \text{H, Me}$; A = single bond, linkage; ALG = I, $\text{CR}_1\text{R}_2\text{R}_3\text{R}_4$, $\text{CH}(\text{OR}_5)\text{R}_6$, II, and $\text{CR}_2\text{R}_3\text{CH}_2\text{R}_4\text{CO}_2\text{R}_5$; $\text{R}_1 = \text{Me, Et, n-Pr, i-Pr, n-Bu, sec-Bu}$; Z = atom. group necessary for forming alicyclic hydrocarbyl (ACHC) together with C; $\text{R}_2\text{-R}_6 = \text{C}_1\text{-4 alkyl}$, ACHC; ≥ 1 of $\text{R}_2\text{-R}_4$ and R_5 and/or R_6 show ACHC; $\text{R}_7\text{-R}_9 = \text{H, C}_1\text{-4 alkyl}$, alicyclic hydrocarbyl; ≥ 1 of $\text{R}_7\text{-R}_9$ show ACHC; R_{10} and/or $\text{R}_{11} = \text{C}_1\text{-4 alkyl}$, ACHC; $\text{R}_{12}\text{-R}_{16} = \text{C}_1\text{-4 alkyl, alicyclic hydrocarbyl}$; ≥ 1 of $\text{R}_{12}\text{-R}_{16} = \text{ACHC}$; R_{17} and R_{18} may be bonded to each other and form ring] and (A2) resins bearing repeating units represented by $\text{CH}_2\text{CR}_2\text{CO}_2\text{A}_1\text{R}_3\text{A}_2\text{CO}_2\text{R}_4$ ($\text{R}_2 = \text{H, alkyl}$; $\text{R}_3 = \text{ACHC}$; $\text{R}_4 = \text{chain-type tertiary alkyl, 1-alkoxyalkyl, tetrahydropyranyl, tetrahydrofuranyl}$; $\text{A}_1, \text{A}_2 = \text{single bond, alkylene, ether, carbonyl, ester}$).

IT 581096-15-3P 581096-72-2P

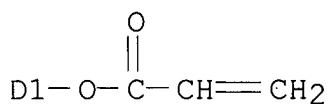
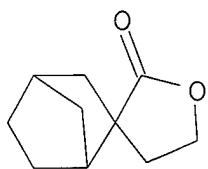
(pos. DUV resist compns. with suppressed roughness of etched surfaces and good dissoln. and defocus latitude in contact hole pattern formation)

RN 581096-15-3 ZCA

CN Tricyclo[3.3.1.13,7]decane-1-carboxylic acid, 3-[(2-methyl-1-oxo-2-propenyl)oxy]-, 1,1-dimethylpropyl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate and 3-hydroxy-5-methyltricyclo[3.3.1.13,7]dec-1-yl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

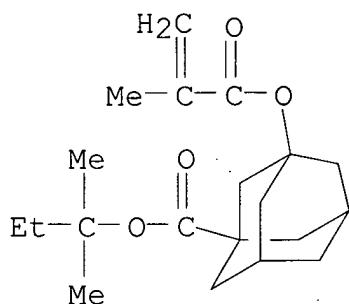
CM 1

CRN 581096-14-2
CMF C13 H16 O4
CCI IDS



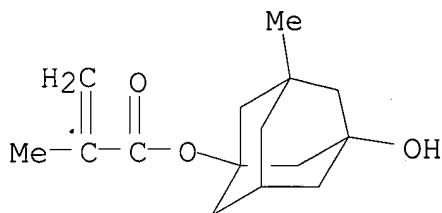
CM 2

CRN 581096-13-1
CMF C20 H30 O4



CM 3

CRN 476312-25-1
CMF C15 H22 O3



RN 581096-72-2 ZCA

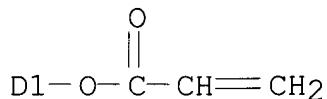
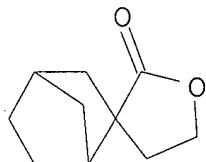
CN 2-Propenoic acid, 2-methyl-, 5-ethyloctahydro-4,7-methano-1H-inden-5-yl ester, polymer with dihydro-2'-oxospiro[bicyclo[2.2.1]heptane-2,3'(2'H)-furan]-5(or 6)-yl 2-propenoate and 2-[[octahydro-1,2(or 2,3)-dihydroxy-4,7-methano-1H-inden-5-yl]oxy]ethyl 2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 581096-14-2

CMF C13 H16 O4

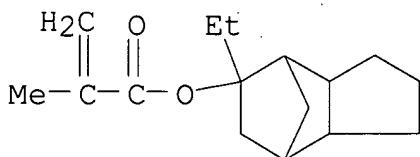
CCI IDS



CM 2

CRN 348089-09-8

CMF C16 H24 O2

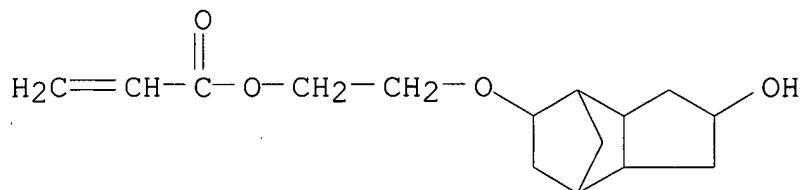


CM 3

CRN 140919-18-2

CMF C15 H22 O5

CCI IDS



D1-OH

IT **581096-15-3P 581096-72-2P**

(pos. DUV resist compns. with suppressed roughness of etched surfaces and good dissoln. and defocus latitude in contact hole pattern formation)